

UNR2211/2212/2213/2214/2215/2216/2217/2218/2219/2210/ 221D/221E/221F/221K/221L/221M/221N/221T/221V/221Z

(UN2211/2212/2213/2214/2215/2216/2217/2218/2219/2210/ 221D/221E/221F/221K/221L/221M/221N/221T/221V/221Z)

Silicon NPN epitaxial planer transistor

For digital circuits

Features

- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- Mini type package, allowing downsizing of the equipment and automatic insertion through tape packing and magazine packing.

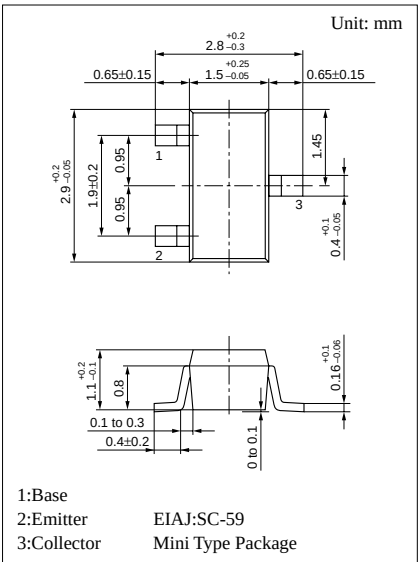
Resistance by Part Number

	Marking Symbol	(R ₁)	(R ₂)
• UNR2211	8A	10kΩ	10kΩ
• UNR2212	8B	22kΩ	22kΩ
• UNR2213	8C	47kΩ	47kΩ
• UNR2214	8D	10kΩ	47kΩ
• UNR2215	8E	10kΩ	—
• UNR2216	8F	4.7kΩ	—
• UNR2217	8H	22kΩ	—
• UNR2218	8I	0.51kΩ	5.1kΩ
• UNR2219	8K	1kΩ	10kΩ
• UNR2210	8L	47kΩ	—
• UNR221D	8M	47kΩ	10kΩ
• UNR221E	8N	47kΩ	22kΩ
• UNR221F	8O	4.7kΩ	10kΩ
• UNR221K	8P	10kΩ	4.7kΩ
• UNR221L	8Q	4.7kΩ	4.7kΩ
• UNR221M	EL	2.2kΩ	47kΩ
• UNR221N	EX	4.7kΩ	47kΩ
• UNR221T	EZ	22kΩ	47kΩ
• UNR221V	FD	2.2kΩ	2.2kΩ
• UNR221Z	FF	4.7kΩ	22kΩ

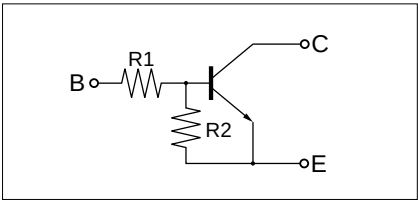
Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	50	V
Collector to emitter voltage	V _{CEO}	50	V
Collector current	I _C	100	mA
Total power dissipation	P _T	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note) The part numbers in the parenthesis show conventional part number.



Internal Connection



UNR2211/2212/2213/2214/2215/2216/2217/2218/2219/2210/
Transistors with built-in Resistor 221D/221E/221F/221K/221L/221M/221N/221T/221V/221Z

■ Electrical Characteristics (T_a=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current		I _{CBO}	V _{CB} = 50V, I _E = 0			0.1	μA
		I _{CEO}	V _{CE} = 50V, I _B = 0			0.5	μA
Emitter cutoff current	UNR2211	I _{EBO}	V _{EB} = 6V, I _C = 0			0.5	mA
	UNR2212/2214/221E/221D/221M/221N/221T					0.2	
	UNR2213					0.1	
	UNR2215/2216/2217/2210					0.01	
	UNR221F/221K					1.0	
	UNR2219					1.5	
	UNR2218/221L/221V					2.0	
	UNR221Z					0.4	
Collector to base voltage		V _{CBO}	I _C = 10μA, I _E = 0	50			V
Collector to emitter voltage		V _{CEO}	I _C = 2mA, I _B = 0	50			V
Forward current transfer ratio	UNR2211	h _{FE}	V _{CE} = 10V, I _C = 5mA	35			
	UNR2212/221E			60			
	UNR2213/2214/221M			80			
	UNR2215*/2216*/2217*/2210*			160		460	
	UNR221F/221D/2219			30			
	UNR2218/221K/221L			20			
	UNR221N/221T			80		400	
	UNR221V			60		200	
	Collector to emitter saturation voltage			V _{CE(sat)}	I _C = 10mA, I _B = 0.3mA		
UNR221V	I _C = 10mA, I _B = 1.5mA		0.04		0.25		
Output voltage high level		V _{OH}	V _{CC} = 5V, V _B = 0.5V, R _L = 1kΩ	4.9			V
Output voltage low level		V _{OL}	V _{CC} = 5V, V _B = 2.5V, R _L = 1kΩ			0.2	V
UNR2213/221K	V _{CC} = 5V, V _B = 3.5V, R _L = 1kΩ				0.2		
UNR221D	V _{CC} = 5V, V _B = 10V, R _L = 1kΩ				0.2		
UNR221E	V _{CC} = 5V, V _B = 6V, R _L = 1kΩ				0.2		
Transition frequency		f _T	V _{CB} = 10V, I _E = -2mA, f = 200MHz		150		MHz
Input resistance	UNR2211/2214/2215/221K	R _i		(−30%)	10	(+30%)	kΩ
	UNR2212/2217/221T				22		
	UNR2213/221D/221E/2210				47		
	UNR2216/221F/221L/221N/221Z				4.7		
	UNR2218				0.51		
	UNR2219				1		
	UNR221M/221V				2.2		

* h_{FE} rank classification (UNR2215/2216/2217/2210)

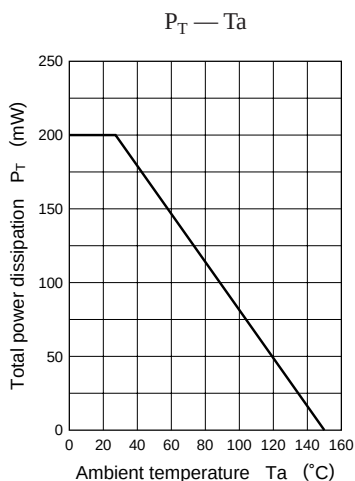
Rank	Q	R	S
h _{FE}	160 to 260	210 to 340	290 to 460

UNR2211/2212/2213/2214/2215/2216/2217/2218/2219/2210/
Transistors with built-in Resistor 221D/221E/221F/221K/221L/221M/221N/221T/221V/221Z

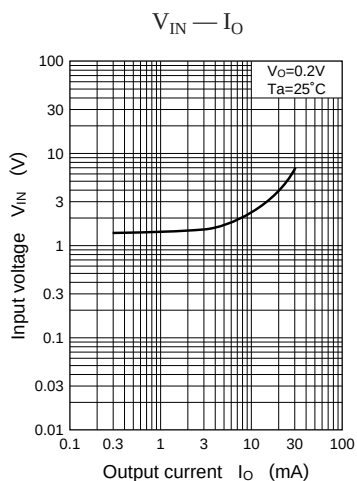
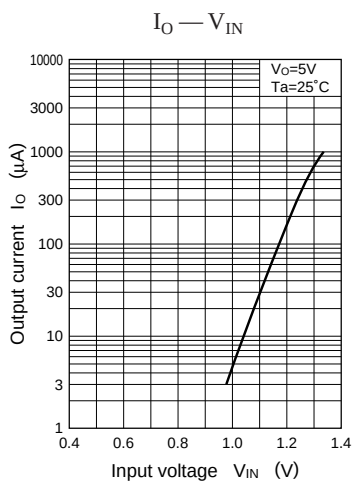
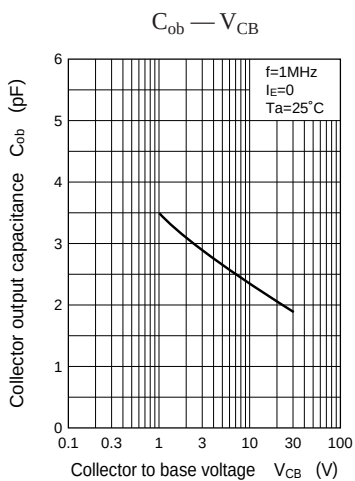
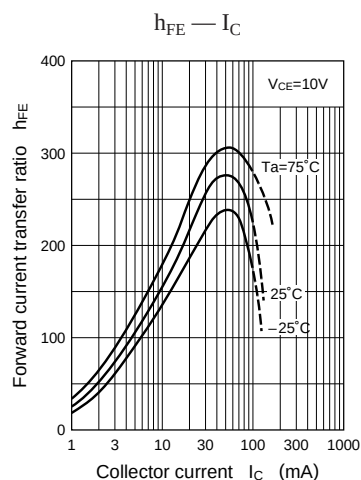
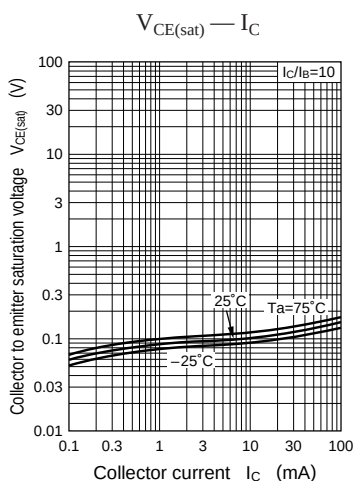
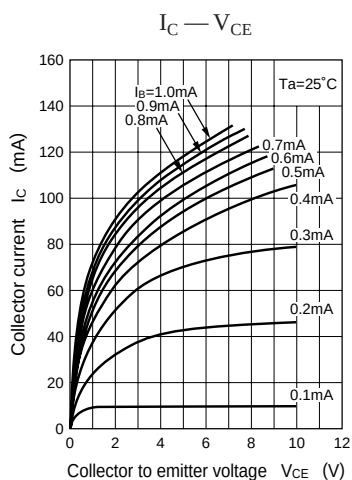
■ Electrical Characteristics (continued) (Ta=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Resis- tance ratio	UNR2211/2212/2213/221L	R_1/R_2		0.8	1.0	1.2	
	UNR2214			0.17	0.21	0.25	
	UNR2218/2219			0.08	0.1	0.12	
	UNR221D				4.7		
	UNR221E				2.14		
	UNR221F/221T				0.47		
	UNR221K				2.13		
	UNR221M				0.047		
	UNR211N				0.1		
	UNR211V				1.0		
	UNR211Z				0.21		

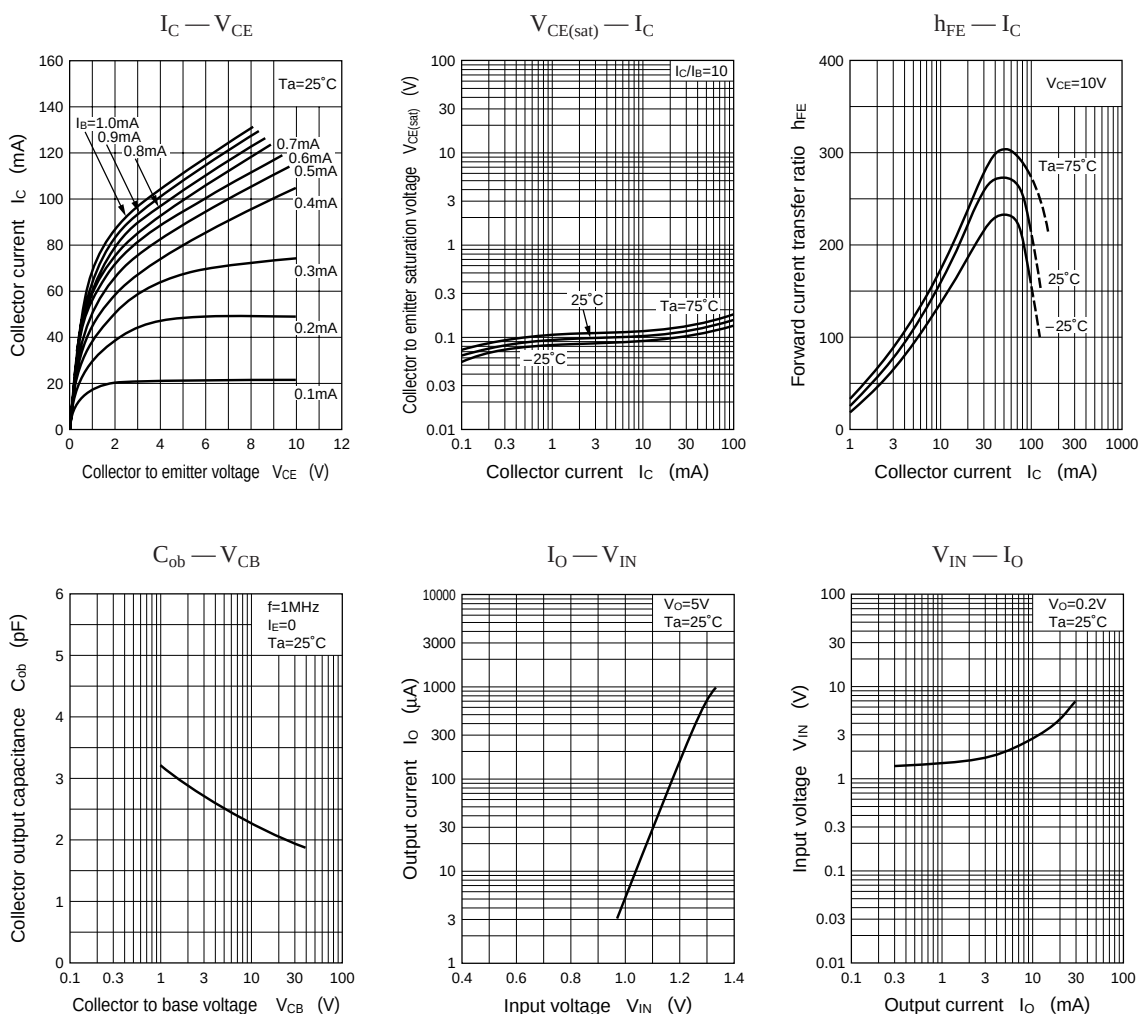
Common characteristics chart



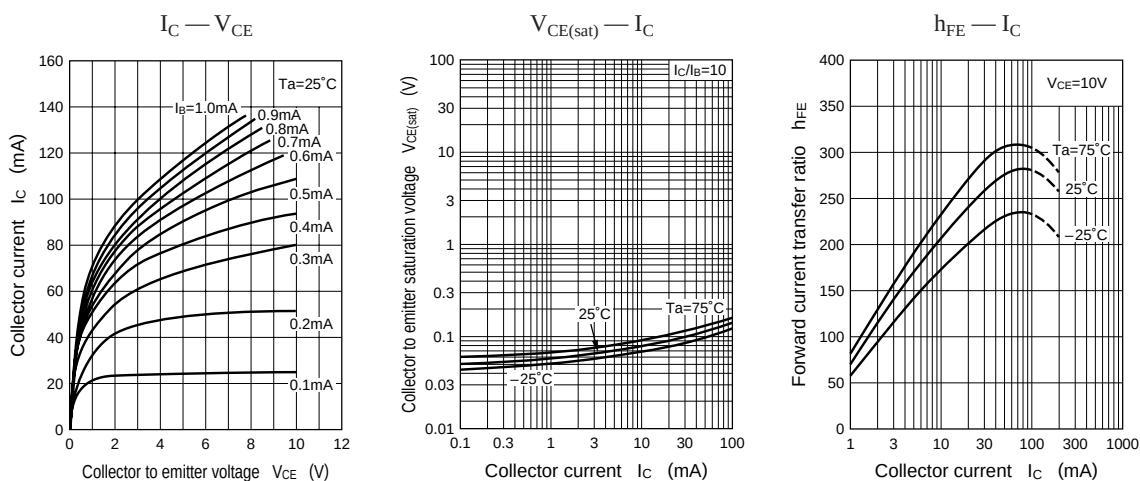
Characteristics charts of UNR2211

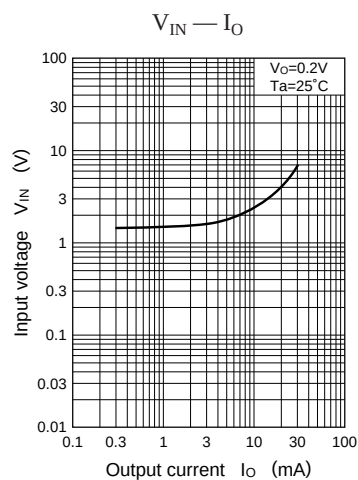
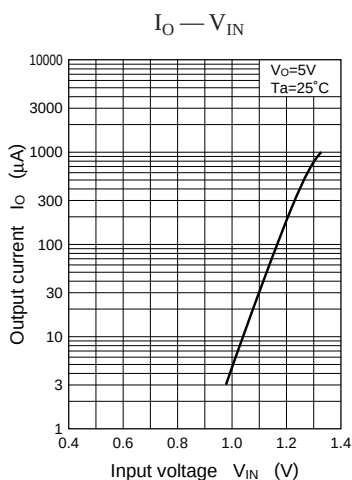
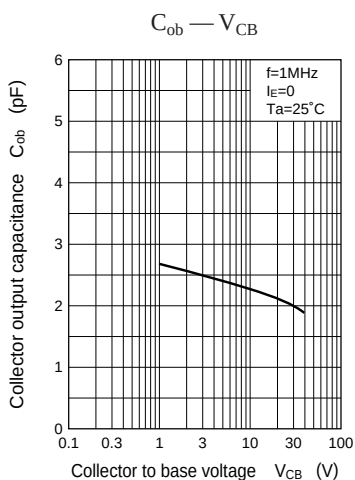


Characteristics charts of UNR2212

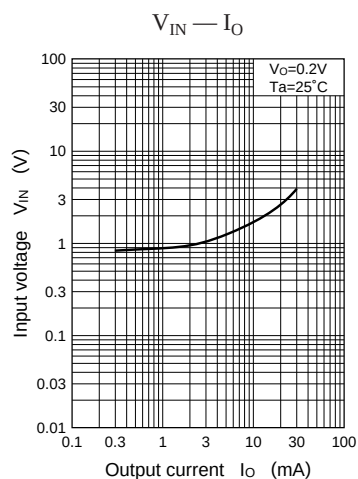
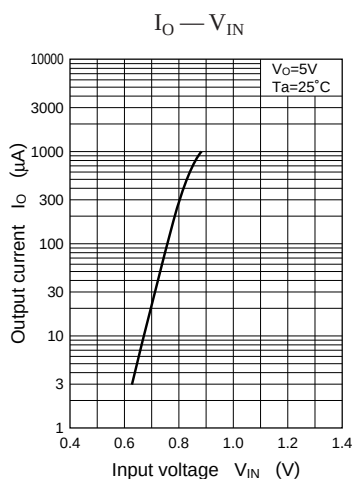
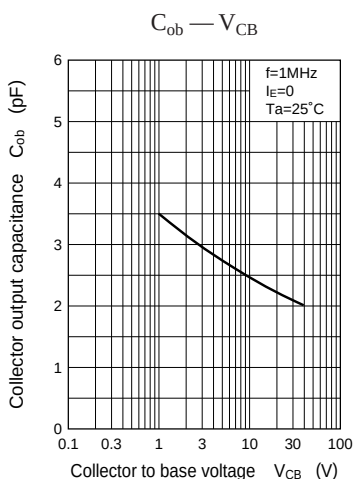
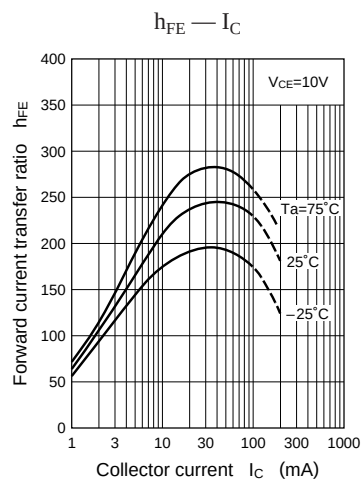
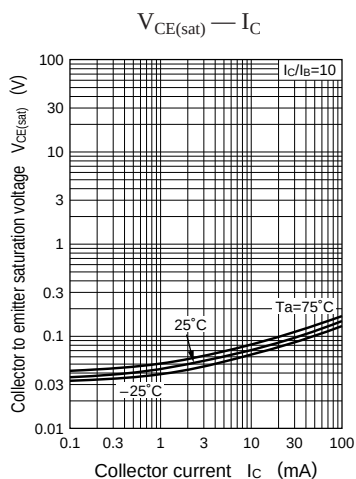
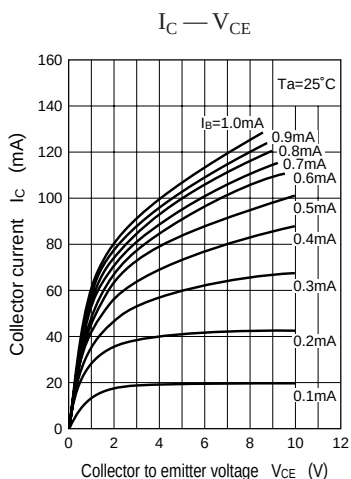


Characteristics charts of UNR2213

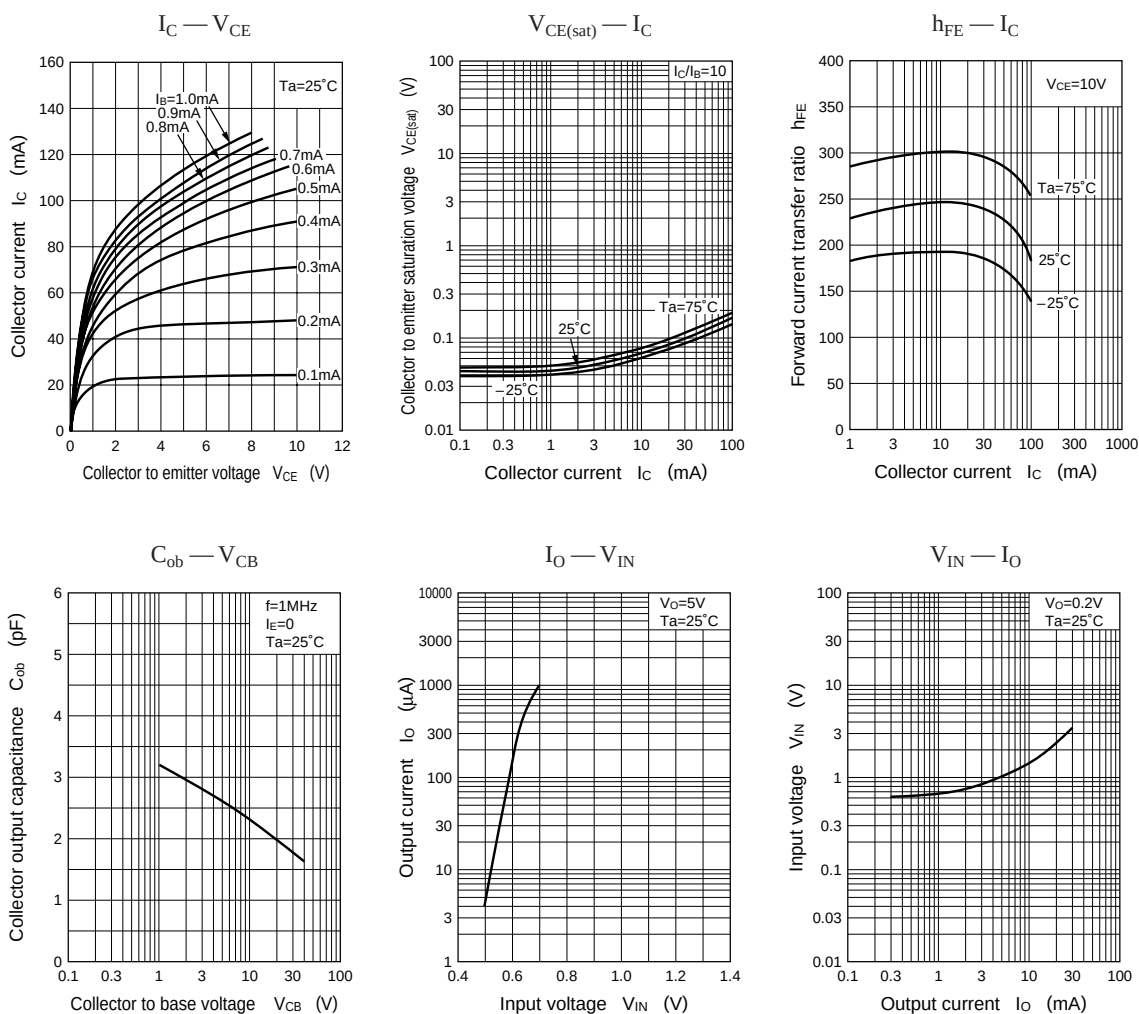




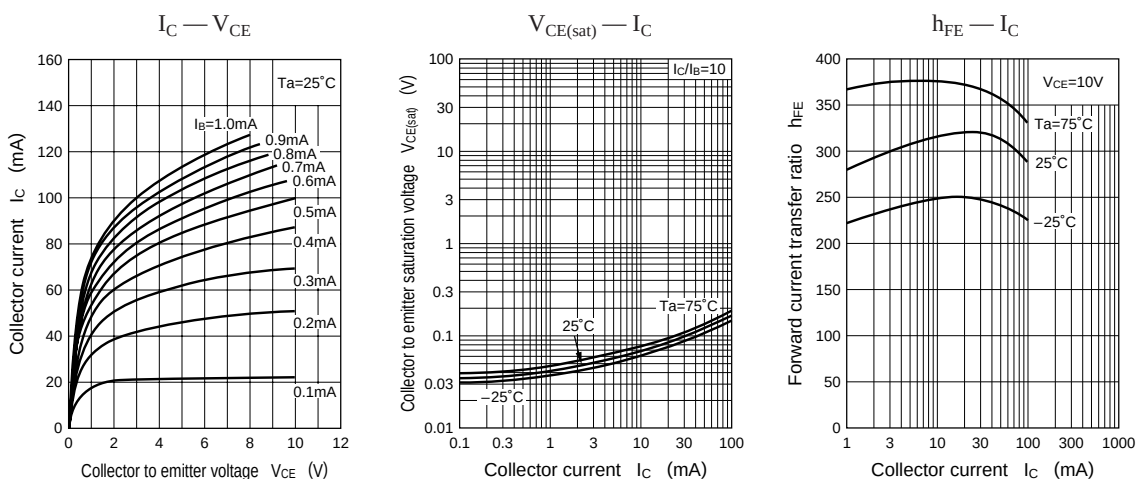
Characteristics charts of UNR2214

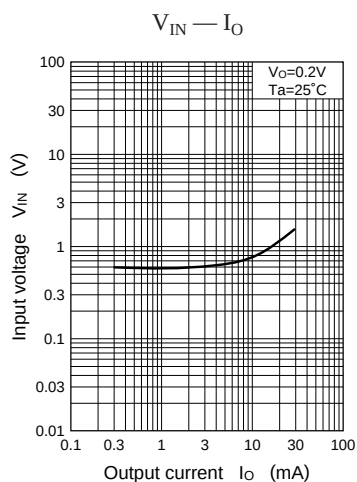
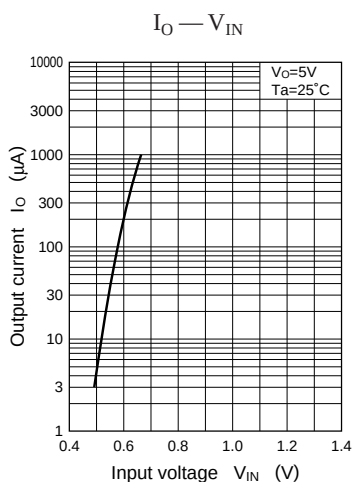
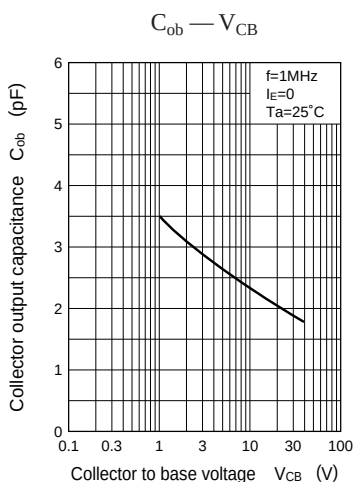


Characteristics charts of UNR2215

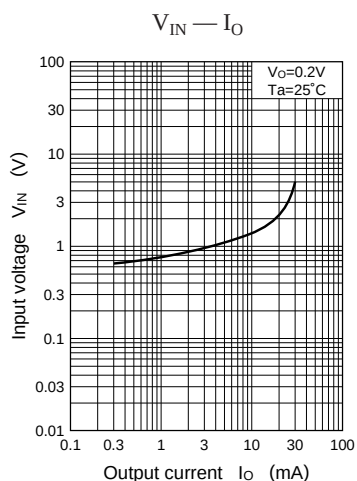
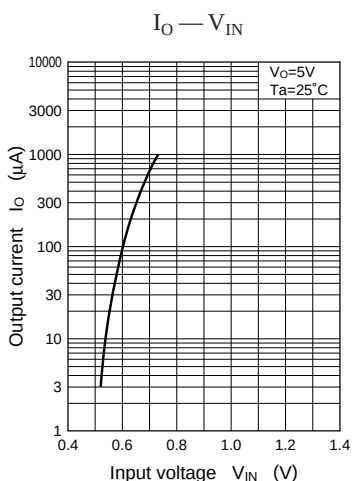
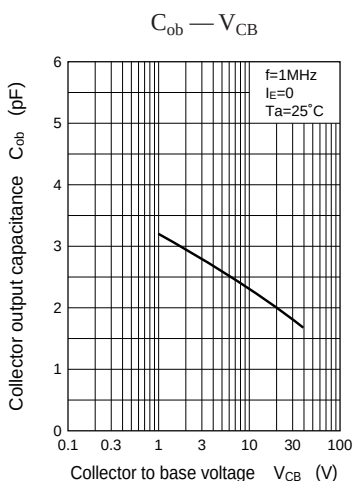
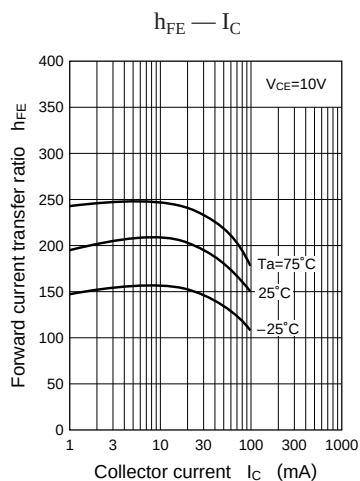
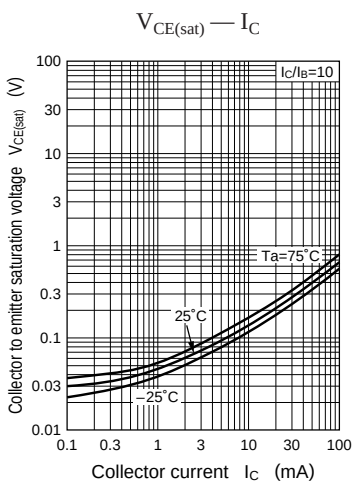
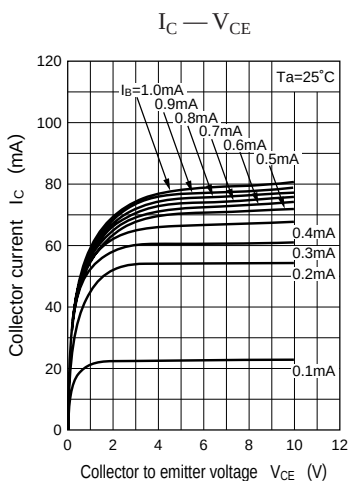


Characteristics charts of UNR2216

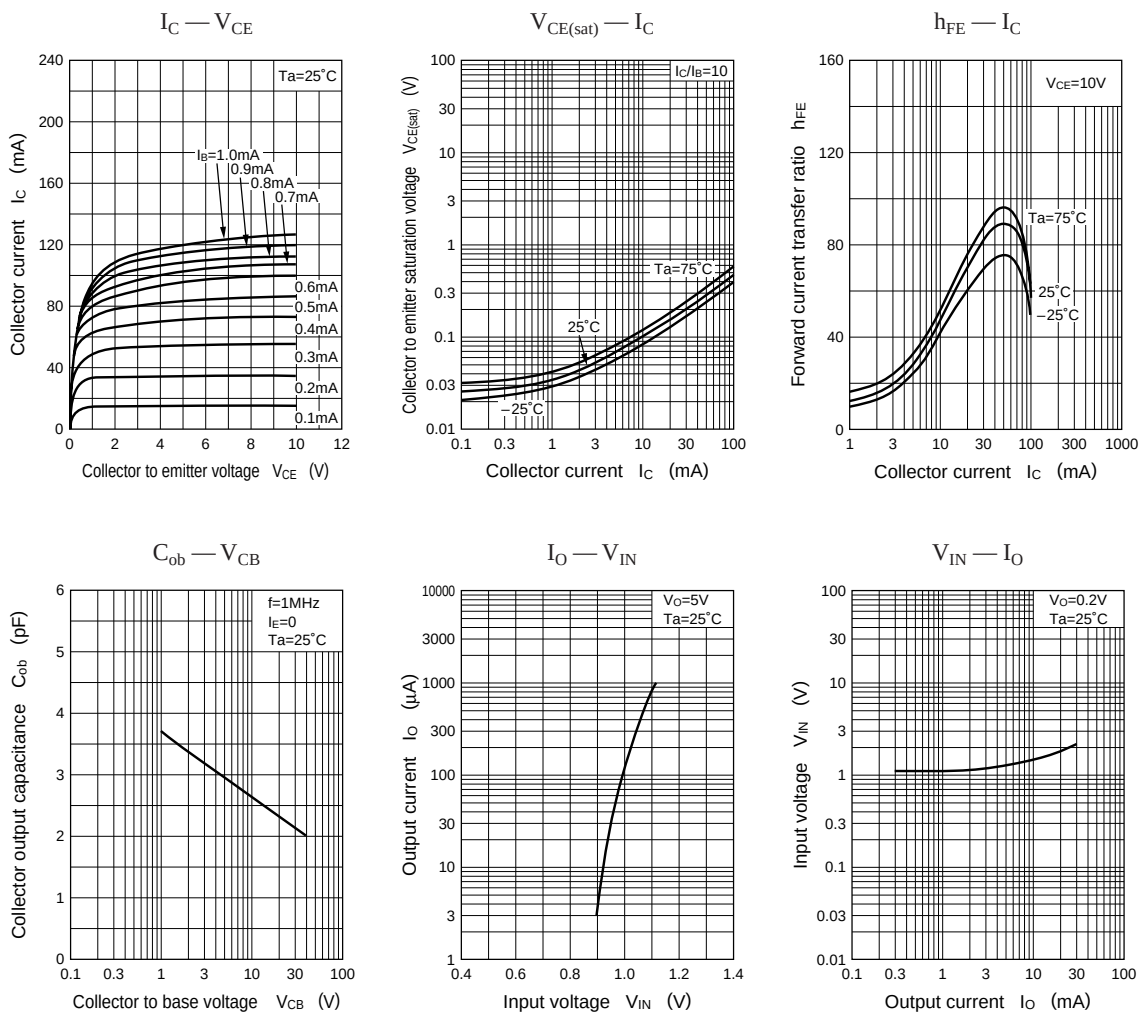




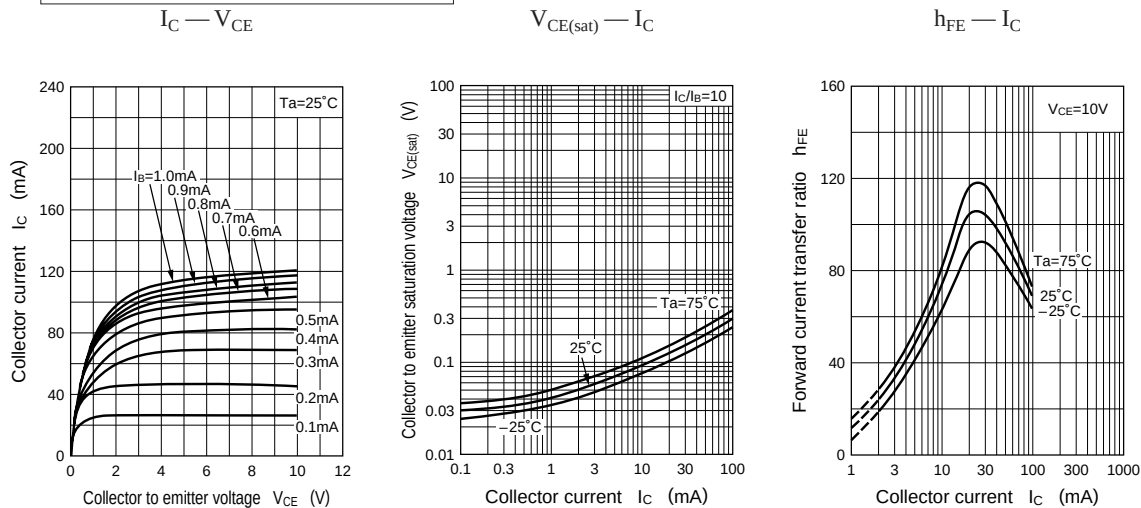
Characteristics charts of UNR2217

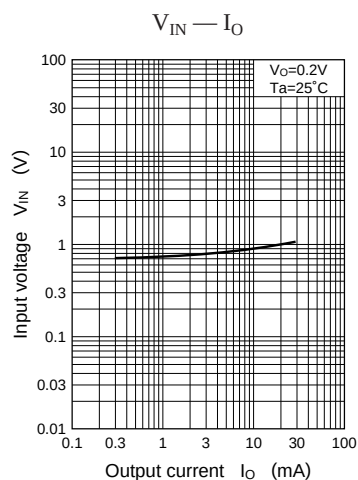
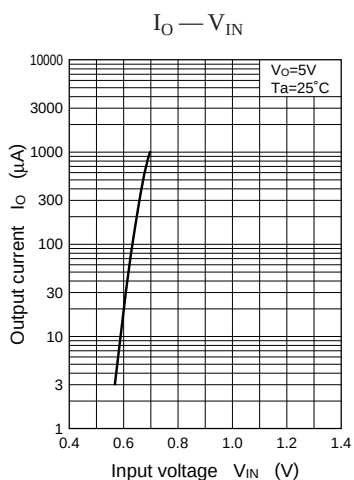
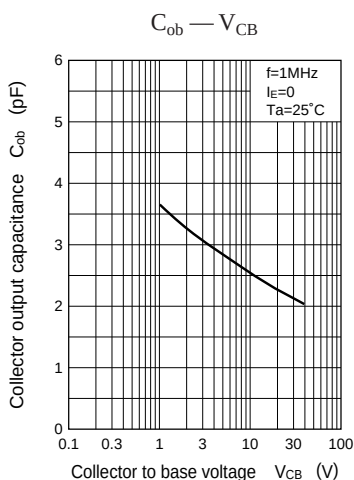


Characteristics charts of UNR2218

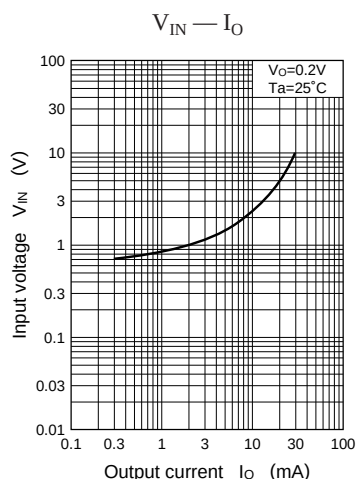
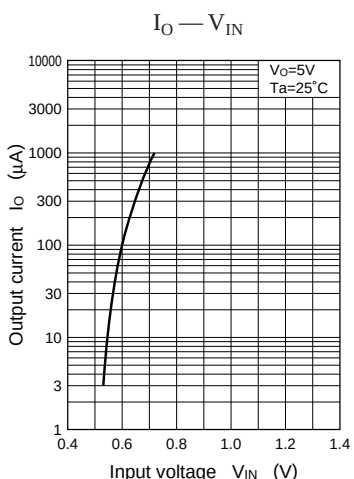
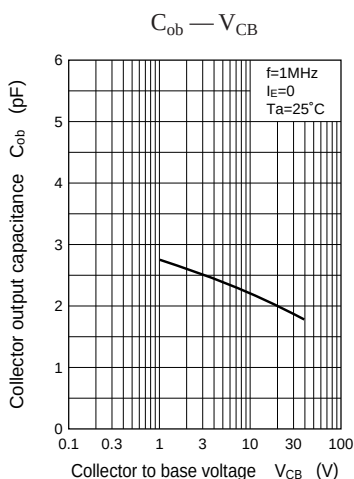
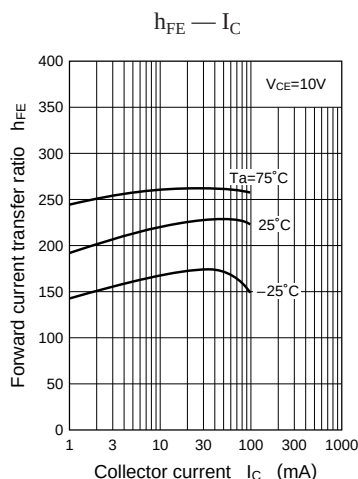
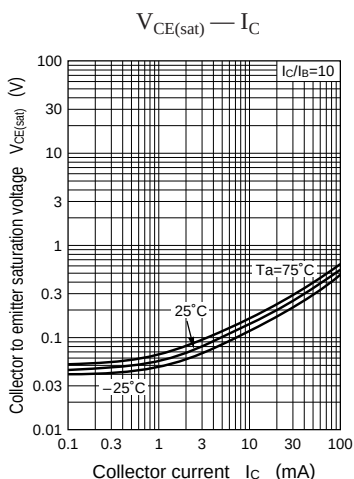
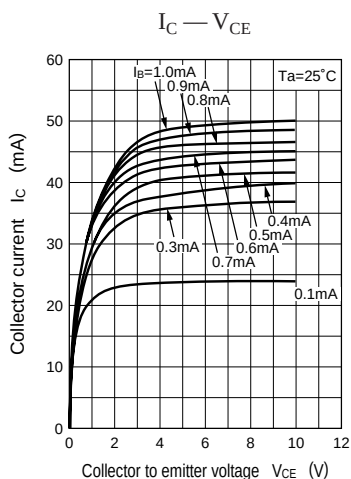


Characteristics charts of UNR2219

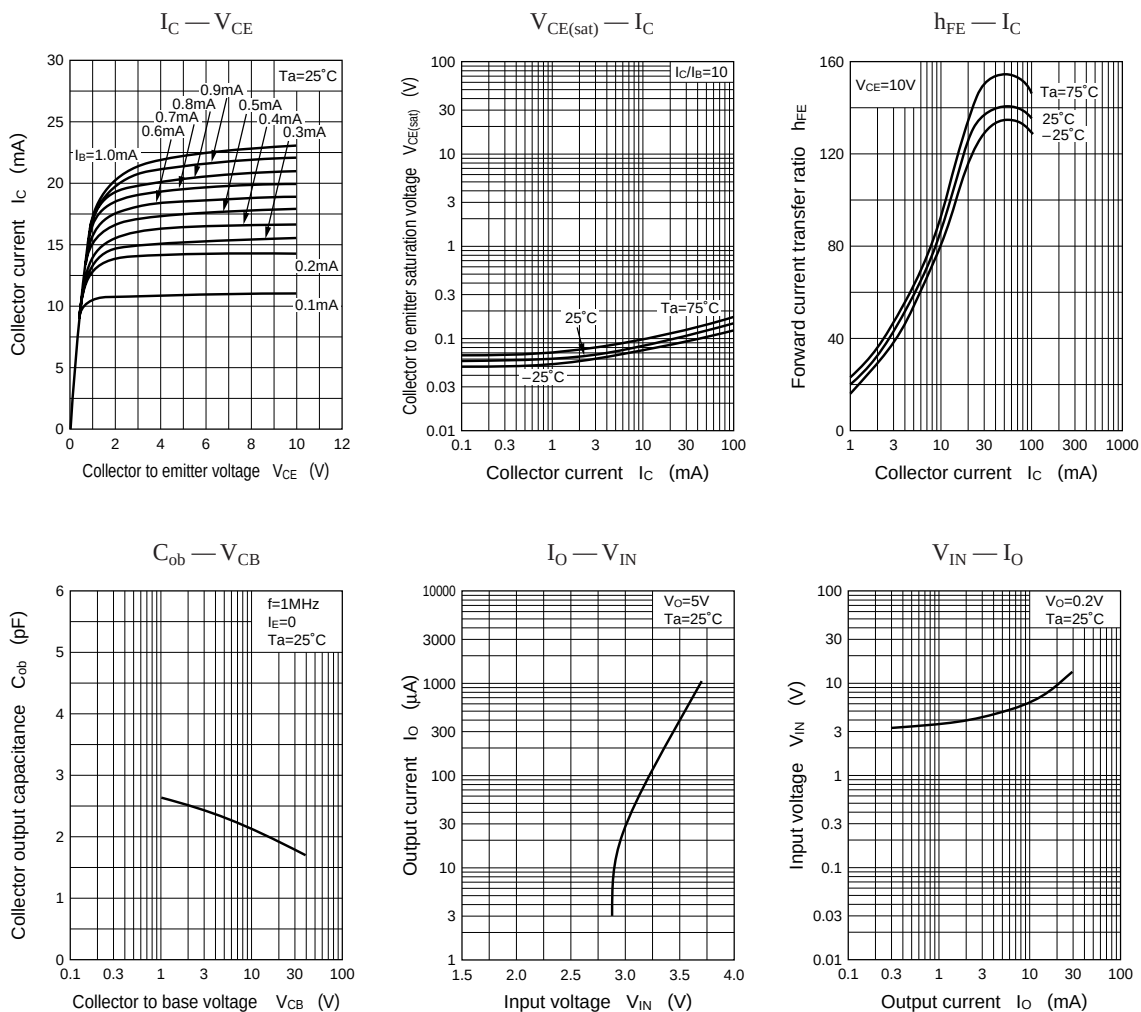




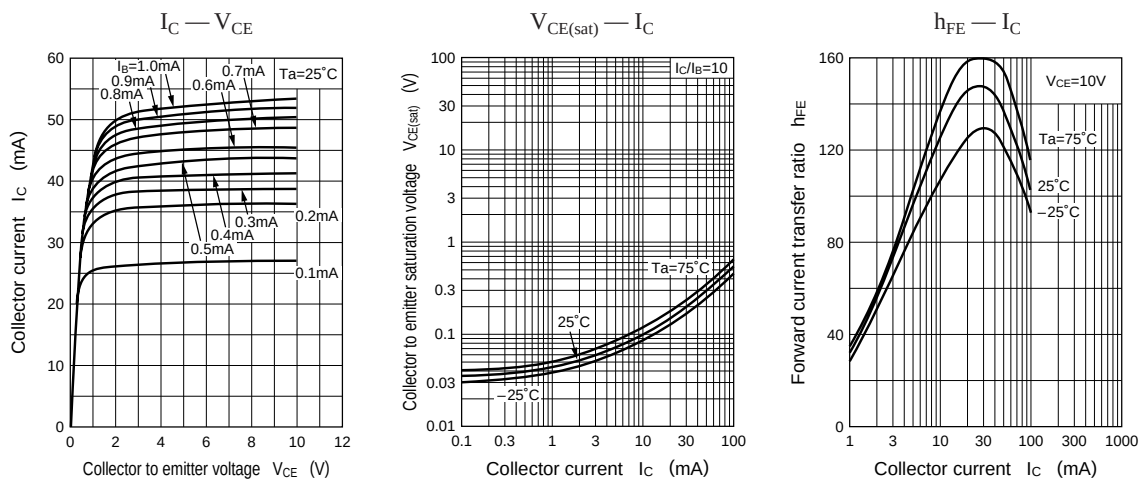
Characteristics charts of UNR2210

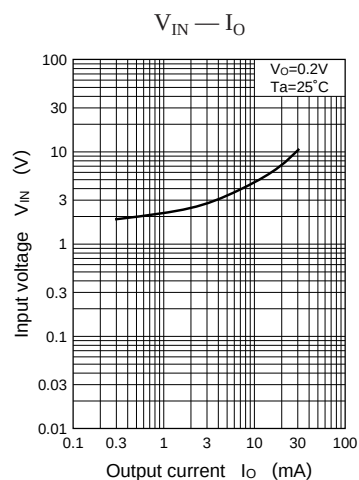
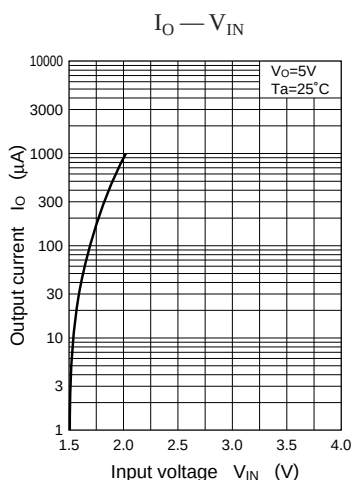
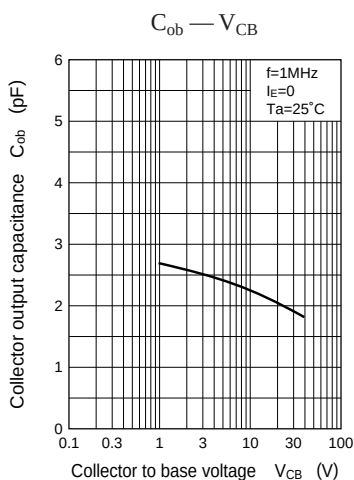


Characteristics charts of UNR221D

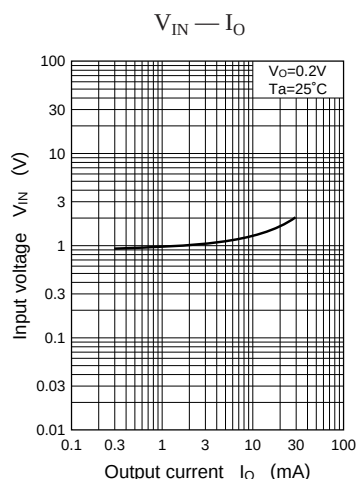
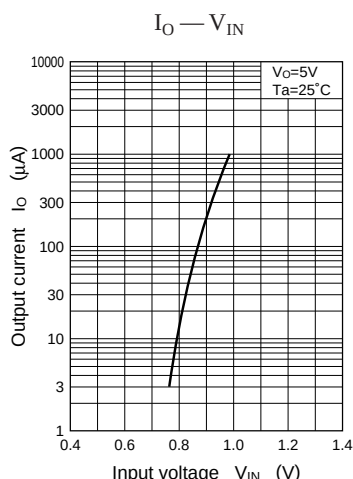
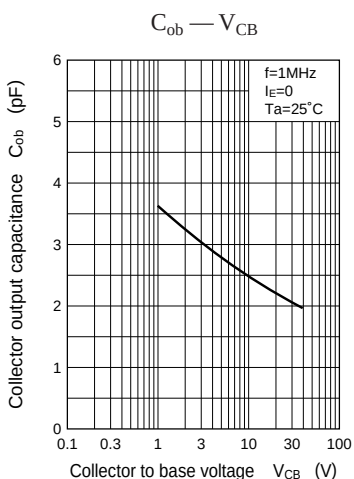
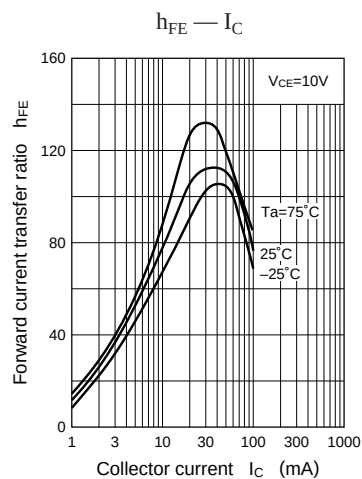
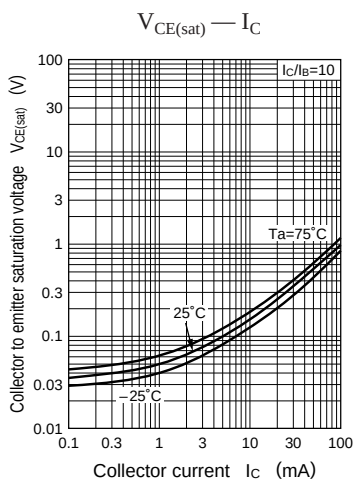
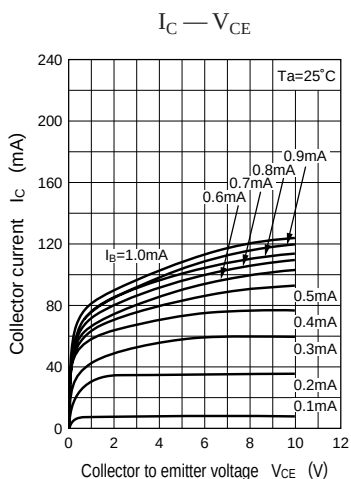


Characteristics charts of UNR221E

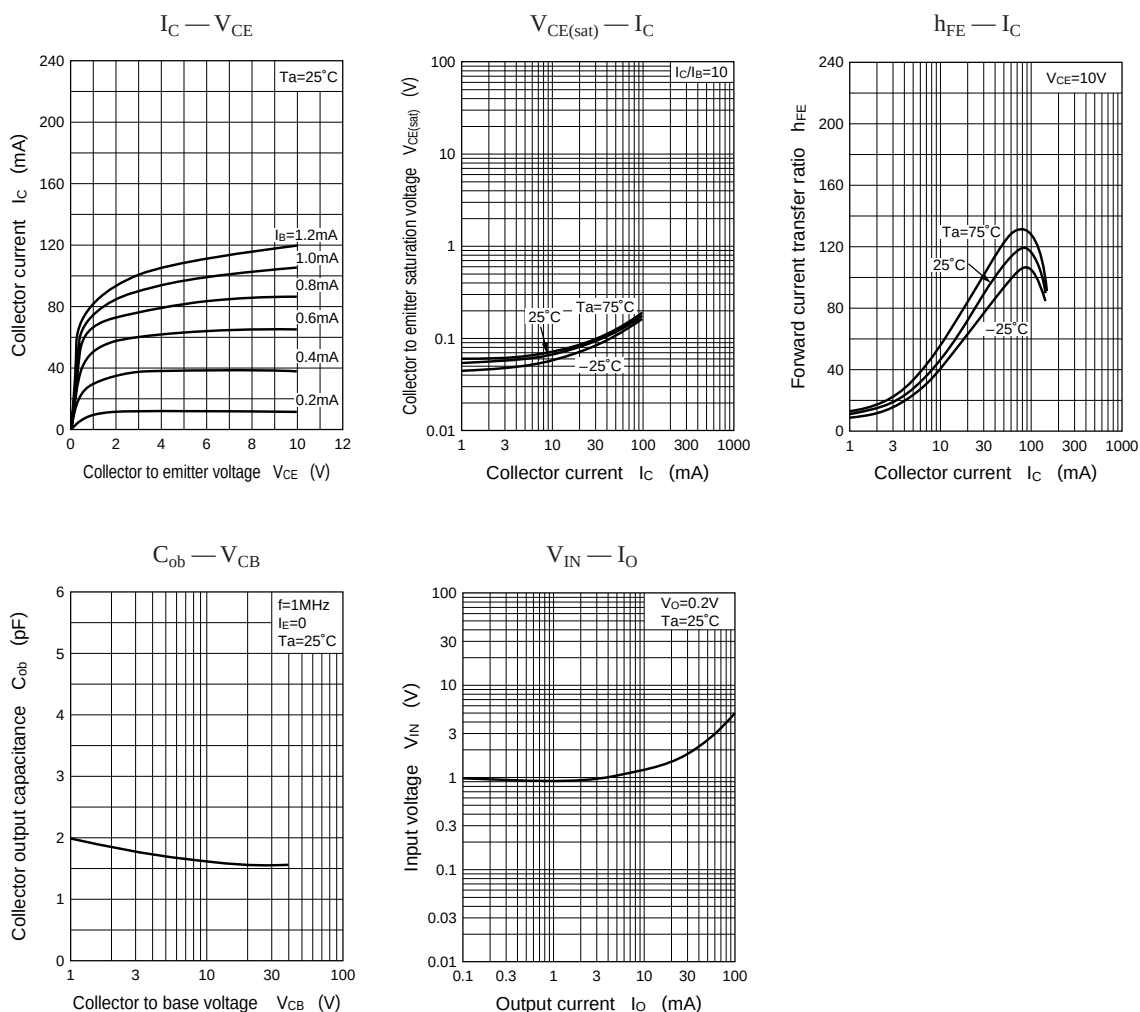




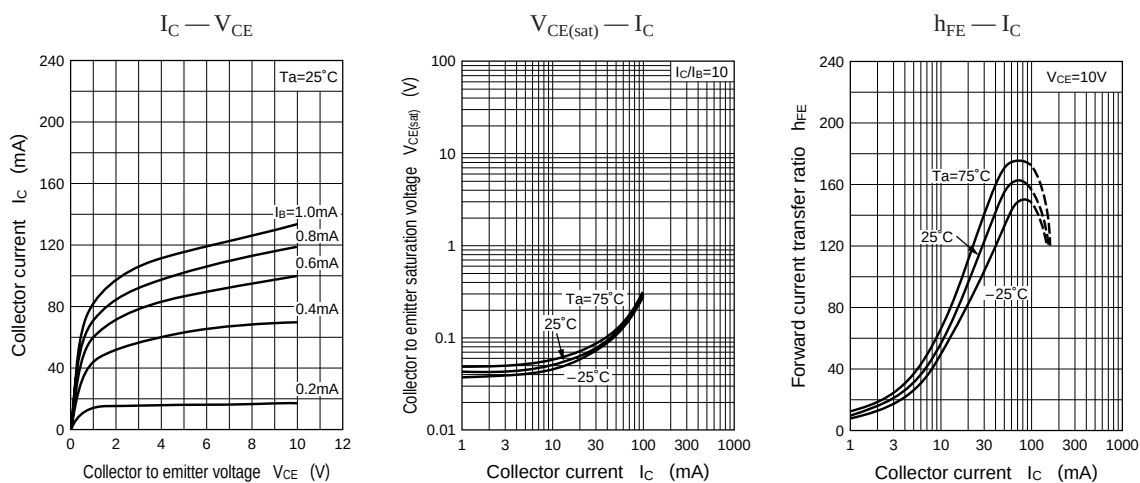
Characteristics charts of UNR221F

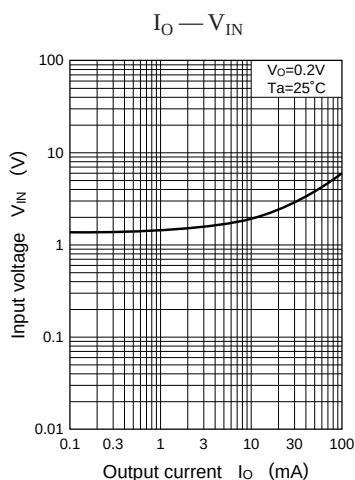
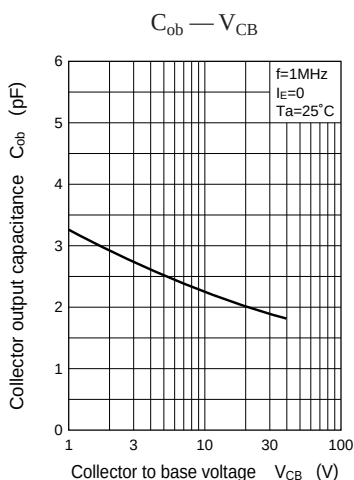


Characteristics charts of UNR221K

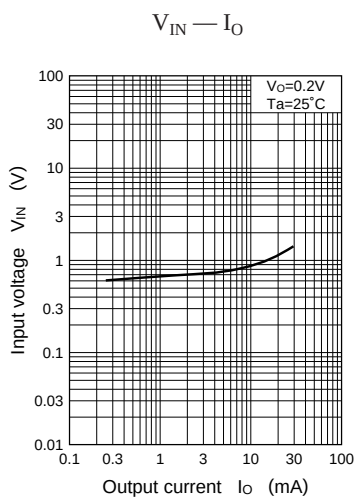
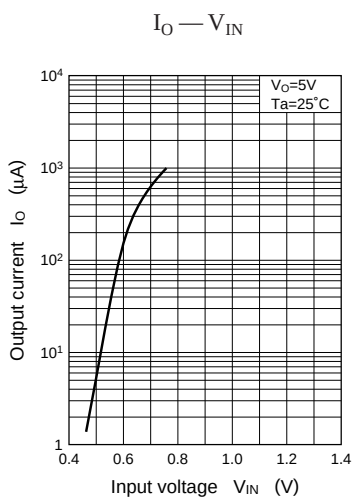
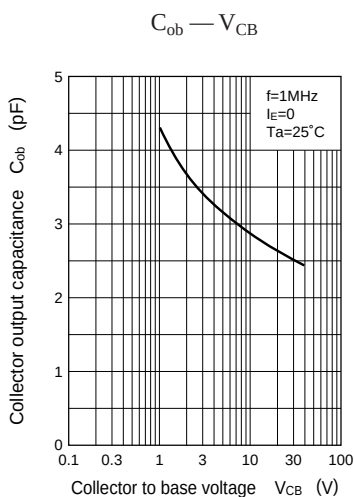
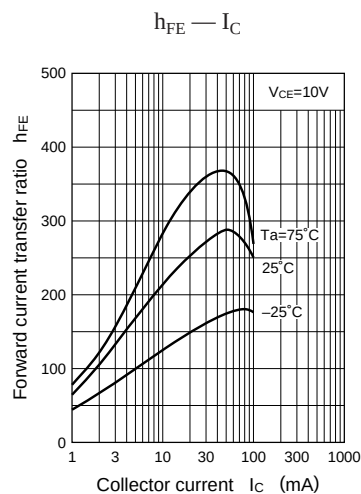
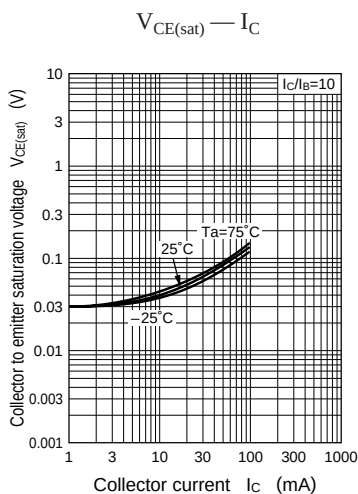
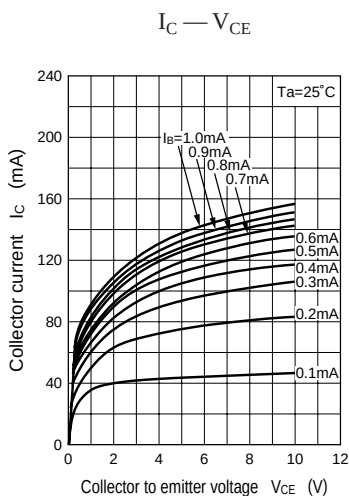


Characteristics charts of UNR221L

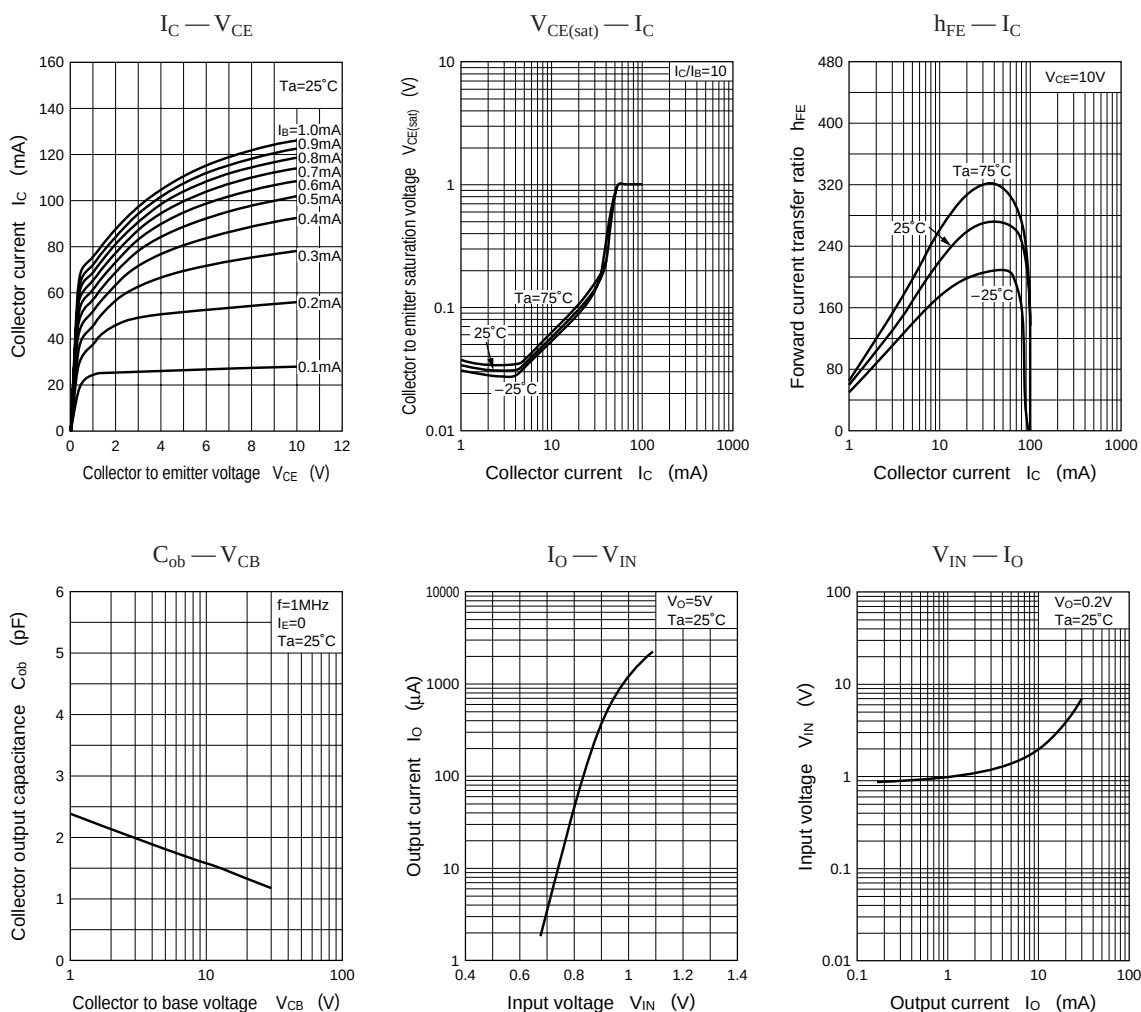




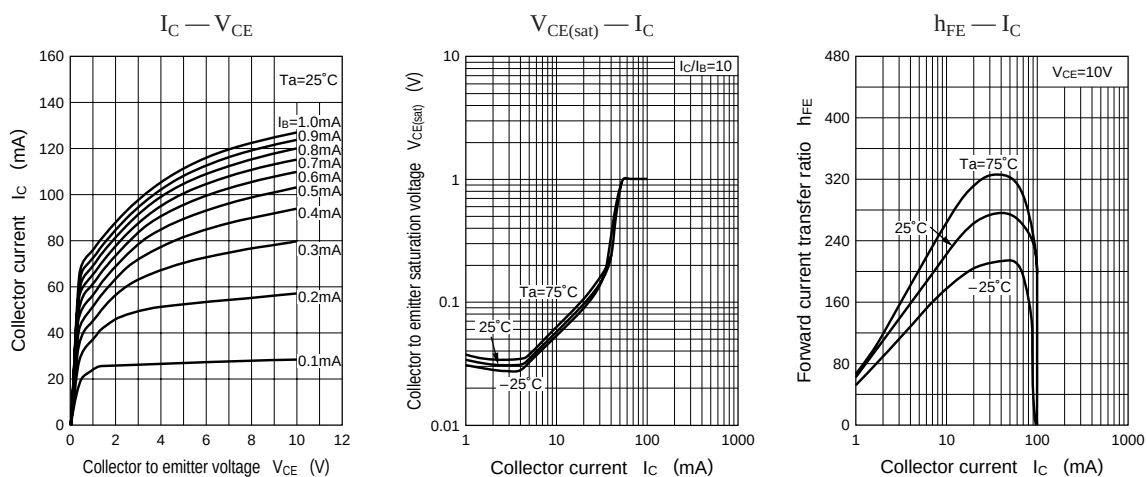
Characteristics charts of UNR221M

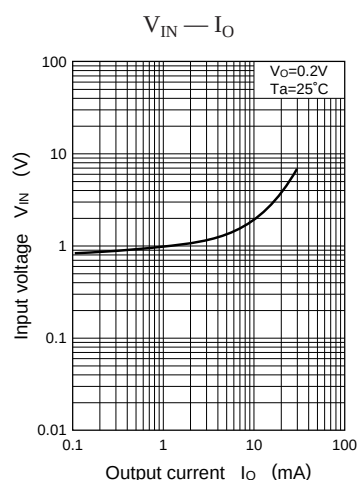
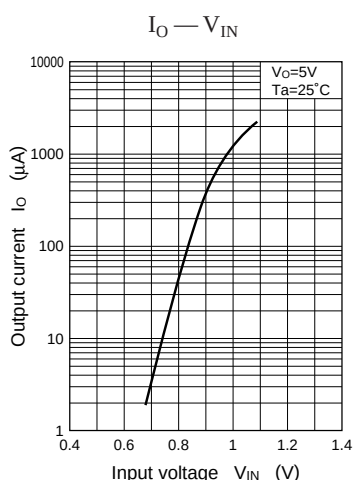
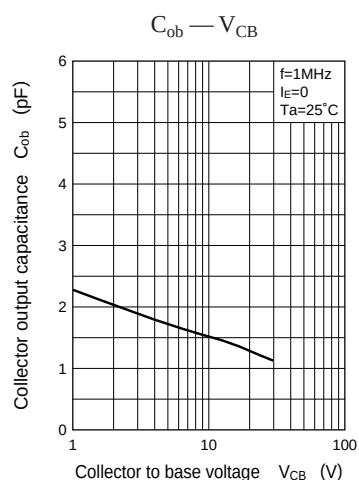


Characteristics charts of UNR221N

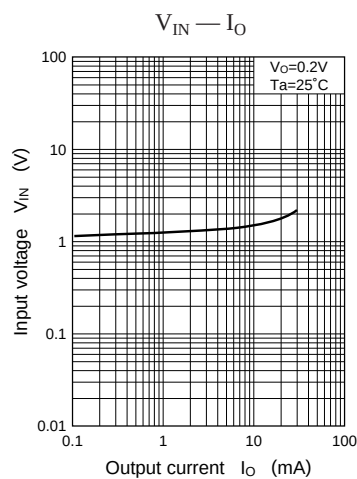
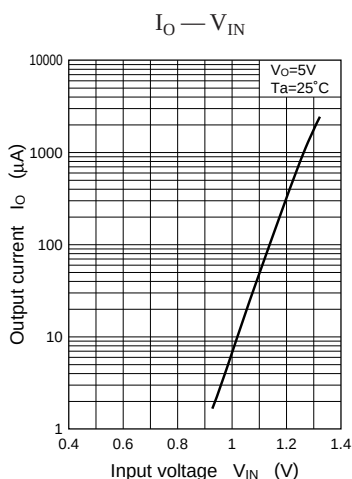
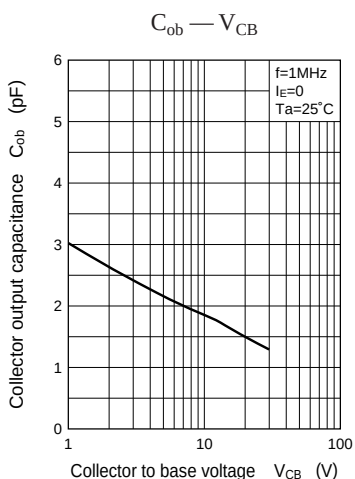
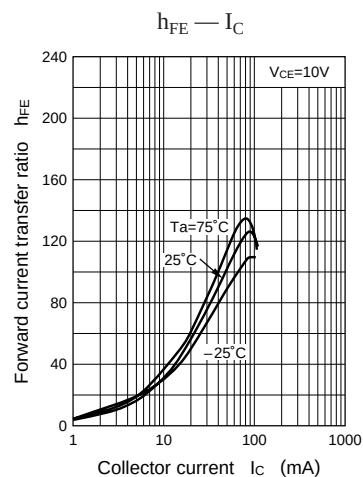
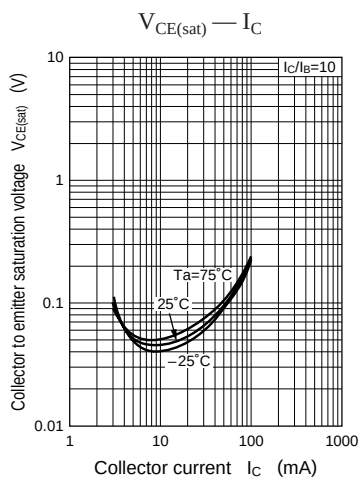
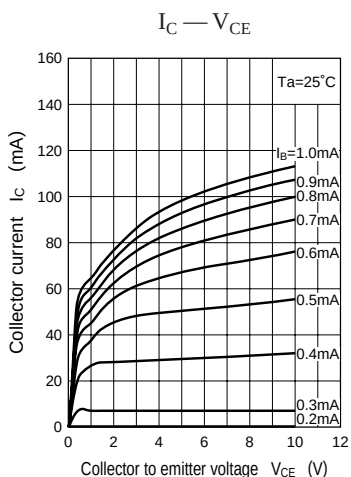


Characteristics charts of UNR221T

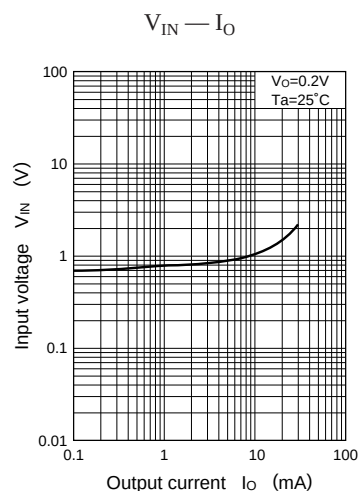
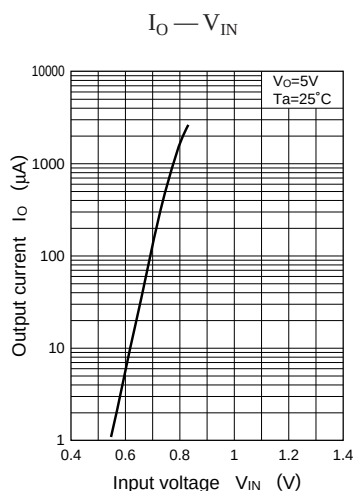
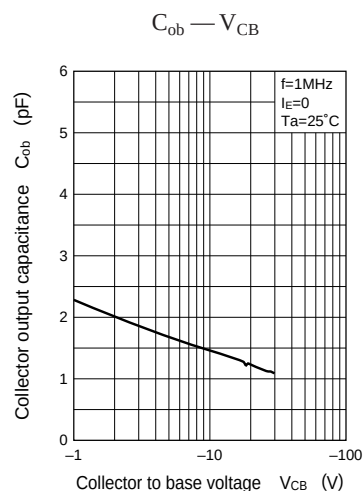
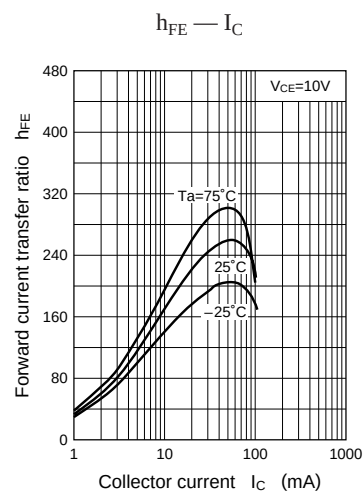
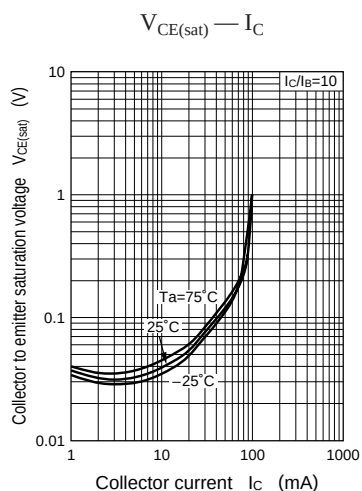
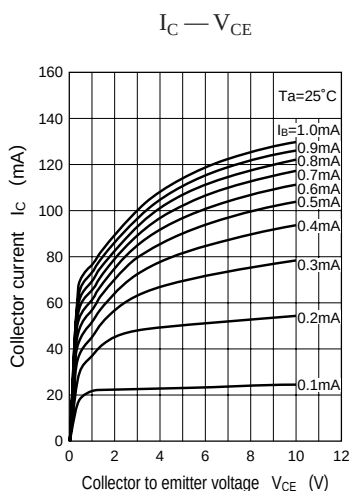




Characteristics charts of UNR221V



Characteristics charts of UNR221Z



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